3.3 V/5 V ECL D Flip-Flop with Reset and Differential Clock

MC10EP51, MC100EP51

Description

The MC10/100EP51 is a differential clock D flip-flop with reset. The device is functionally equivalent to the EL51 and LVEL51 devices.

The reset input is an asynchronous, level triggered signal. Data enters the master portion of the flip–flop when the clock is LOW and is transferred to the slave, and thus the outputs, upon a positive transition of the clock. The differential clock inputs of the EP51 allow the device to be used as a negative edge triggered flip-flop.

The differential input employs clamp circuitry to maintain stability under open input conditions. When left open, the CLK input will be pulled down to V_{EE} and the \overline{CLK} input will be biased at $V_{CC}/2$.

The 100 Series contains temperature compensation.

Features

- 350 ps Typical Propagation Delay
- Maximum Frequency > 3 GHz Typical
- PECL Mode Operating Range: $V_{CC} = 3.0 \text{ V}$ to 5.5 V with $V_{EE} = 0 \text{ V}$
- NECL Mode Operating Range: $V_{CC} = 0 V$ with $V_{EE} = -3.0 V$ to -5.5 V
- Open Input Default State
- Safety Clamp on Inputs
- These Devices are Pb-Free and are RoHS Compliant

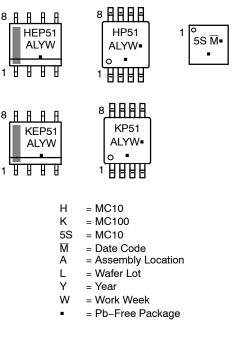


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MARKING DIAGRAMS*



(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

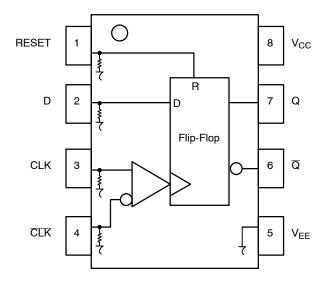


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

PIN	FUNCTION						
CLK*, CLK*	ECL Clock Inputs						
Reset*	ECL Asynchronous Reset						
D*	ECL Data Input						
Q, <u>Q</u>	ECL Data Outputs						
V _{CC}	Positive Supply						
V _{EE}	Negative Supply						
EP	(DFN8 only) Thermal exposed pad must be connected to a suf- ficient thermal conduit. Electric- ally connect to the most negative supply (GND) or leave uncon- nected, floating open.						

* Pins will default LOW when left open.

Table 2. TRUTH TABLE

D	R	CLK	Q
L	L	Z	L
н	L	Z	н
X	Н	Х	L

Z = LOW to HIGH Transition

Table 3. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 2 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 TSSOP-8 DFN8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in
Transistor Count	165 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	•

1. For additional information, see Application Note <u>AND8003/D</u>.

Table 4. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V_{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-6	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage			6 _6	V V
I _{out}	Output Current	Continuous Surge		50 100	mA mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 SOIC-8	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	(Note 2)	DFN8	35 to 40	°C/W
T _{sol}	Wave Solder Pb Pb-Free			265 265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power).

Table 5. 10EP DC CHARACTERISTICS, PECL V_{CC} = 3.3 V, V_{EE} = 0 V (Note 3)

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	26	34	44	26	35	45	28	37	47	mA
V _{OH}	Output HIGH Voltage (Note 4)	2165	2290	2415	2230	2355	2480	2290	2415	2540	mV
V _{OL}	Output LOW Voltage (Note 4)	1365	1490	1615	1430	1555	1680	1490	1615	1740	mV
VIH	Input HIGH Voltage (Single-Ended)	2090		2415	2155		2480	2215		2540	mV
V_{IL}	Input LOW Voltage (Single-Ended)	1365		1690	1430		1755	1490		1815	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 5)	2.0		3.3	2.0		3.3	2.0		3.3	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
۱ _{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

3. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.3 V to -2.2 V. 4. All loading with 50 Ω to V_{CC} - 2.0 V. 5. V_{HCMR} min varies 1:1 with V_{EE} , V_{HCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

–40°C 25°C 85°C Characteristic Symbol Min Тур Max Min Тур Max Min Тур Max Unit IEE **Power Supply Current** 26 34 44 26 35 45 28 37 47 mΑ VOH Output HIGH Voltage (Note 7) 3865 3990 4115 3930 4055 4180 3990 4115 4240 mV Output LOW Voltage (Note 7) VOL 3065 3190 3315 3130 3255 3380 3190 3315 3440 mV VIH Input HIGH Voltage (Single-Ended) 3790 4115 3855 4180 3915 4240 mV VIL Input LOW Voltage (Single-Ended) 3065 3390 3130 3455 3190 3515 mV Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 8) V VIHCMR 5.0 2.0 2.0 5.0 2.0 5.0 I_{IH} Input HIGH Current 150 150 150 μA Input LOW Current 0.5 0.5 0.5 $I_{\parallel \perp}$ μA

Table 6. 10EP DC CHARACTERISTICS, PECL V_{CC} = 5.0 V, V_{EE} = 0 V (Note 6)

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

6. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +2.0 V to –0.5 V.

7. All loading with 50 Ω to V_{CC} – 2.0 V. 8. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 7. 10EP DC CHARACTERISTICS, NECL Vo	V _{CC} = 0 V; V _{EE} = -5.5 V to -3.0 V (Note 9)
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			–40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	
I _{EE}	Power Supply Current	23	30	40	23	30	40	23	30	40	mA	
I _{EE}	Power Supply Current	26	34	44	26	35	45	28	37	47	mA	
VOH	Output HIGH Voltage (Note 10)	-1135	-1010	-885	-1070	-945	-820	-1010	-885	-760	mV	
V _{OL}	Output LOW Voltage (Note 10)	-1935	-1810	-1685	-1870	-1745	-1620	-1810	-1685	-1560	mV	
V _{IH}	Input HIGH Voltage (Single-Ended)	-1210		-885	-1145		-820	-1085		-760	mV	
V _{IL}	Input LOW Voltage (Single-Ended)	-1935		-1610	-1870		-1545	-1810		-1485	mV	
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 11)	V _{EE} ·	V _{EE} + 2.0		V _{EE}	+ 2.0	0.0	V _{EE} ·	+ 2.0	0.0	V	
I _{IH}	Input HIGH Current			150			150			150	μA	
١ _{IL}	Input LOW Current	0.5			0.5			0.5			μA	

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

9. Input and output parameters vary 1:1 with V_{CC}.

10. All loading with 50 Ω to V_{CC} – 2.0 V.

11. VIHCMR min varies 1:1 with VEE, VIHCMR max varies 1:1 with VCC. The VIHCMR range is referenced to the most positive side of the differential input signal.

-40°C 25°C 85°C Symbol Characteristic Min Тур Max Min Тур Max Min Тур Max Unit IEE **Power Supply Current** 26 34 44 26 35 45 28 37 47 mΑ VOH Output HIGH Voltage (Note 13) 2155 2280 2405 2155 2280 2405 2155 2280 2405 mV VOL Output LOW Voltage (Note 13) 1355 1480 1605 1355 1480 1605 1355 1480 1605 mV 2075 2075 2420 VIH Input HIGH Voltage (Single-Ended) 2420 2075 2420 mV VIL Input LOW Voltage (Single-Ended) 1355 1675 1355 1675 1355 1675 mV V VIHCMR Input HIGH Voltage Common Mode Range 2.0 3.3 2.0 3.3 2.0 3.3 (Differential Configuration) (Note 14) Input HIGH Current 150 150 150 lιH μΑ Input LOW Current Iп 0.5 0.5 0.5 μA

Table 8. 100EP DC CHARACTERISTICS, PECL V_{CC} = 3.3 V, V_{EE} = 0 V (Note 12)

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

12. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to -2.2 V.

13. All loading with 50 Ω to V_{CC} – 2.0 V. 14. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 9. 100EP DC CHARACTERISTICS, PECL V_{CC} = 5.0 V, V_{EE} = 0 V (Note 15)

		-40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	26	34	44	26	35	45	28	37	47	mA
V _{OH}	Output HIGH Voltage (Note 16)	3855	3980	4105	3855	3980	4105	3855	3980	4105	mV
V _{OL}	Output LOW Voltage (Note 16)	3055	3180	3305	3055	3180	3305	3055	3180	3305	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	3775		4120	3775		4120	3775		4120	mV
V _{IL}	Input LOW Voltage (Single-Ended)	3055		3375	3055		3375	3055		3375	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 17)	2.0		5.0	2.0		5.0	2.0		5.0	V
I _{IH}	Input HIGH Current			150			150			150	μA
۱ _{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

15. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +2.0 V to –0.5 V.

16. All loading with 50 Ω to V_{CC} – 2.0 V.
17. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	26	34	44	26	35	45	28	37	47	mA
V _{OH}	Output HIGH Voltage (Note 19)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V _{OL}	Output LOW Voltage (Note 19)	-1945	-1820	-1695	-1945	-1820	-1695	-1945	-1820	-1695	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
VIL	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 20)	VEE	+ 2.0	0.0	V _{EE}	+ 2.0	0.0	V _{EE}	+ 2.0	0.0	V
Ι _{ΙΗ}	Input HIGH Current			150			150			150	μA
١ _{IL}	Input LOW Current	0.5			0.5			0.5			μA

Table 10. 100EP DC CHARACTERISTICS, NECL V_{CC} = 0 V; V_{EE} = -5.5 V to -3.0 V (Note 18)

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

18. Input and output parameters vary 1:1 with V_{CC}.
19. All loading with 50 Ω to V_{CC} – 2.0 V.
20. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 11. AC CHARACTERISTICS V _{CC} = 0 V; V _{EE} = -	-3.0 V to -5.5 V or V _{CC} = 3.0 V to 5.5 V; V _{EE} = 0 V (Note 21)
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			−40°C			25°C		85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Frequency (Figure 2)		> 3			> 3			> 3		GHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential CLK, CLK to Q, Q 10 100 RESET to Q, Q		300 340 380	350 425 450	270 300 325	320 375 400	370 450 475	300 350 350	350 425 425	420 500 500	ps
t _{RR}	Reset Recovery	150			150			150			ps
t _S t _H	Setup Time Hold Time	100 100			100 100	80 40		100 100			ps
t _{PW}	Minimum Pulse Width RESET	500	440		500	440		500	440		ps
t JITTER	Cycle-to-Cycle Jitter (Figure 2)		0.2	< 1		0.2	< 1		0.2	< 1	ps
t _r t _f	Output Rise/Fall Times Q, Q (20% - 80%) Q	70	120	170	80	130	180	100	150	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

21. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

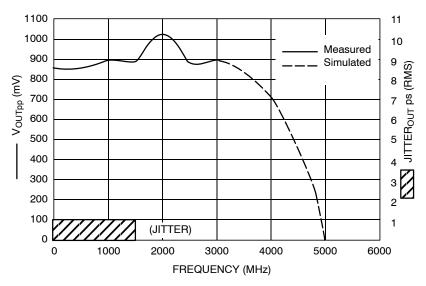


Figure 2. F_{max}/Jitter

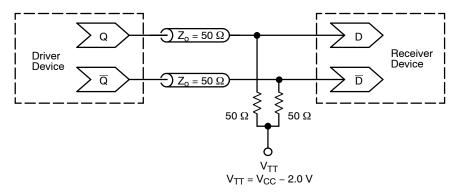


Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices.)

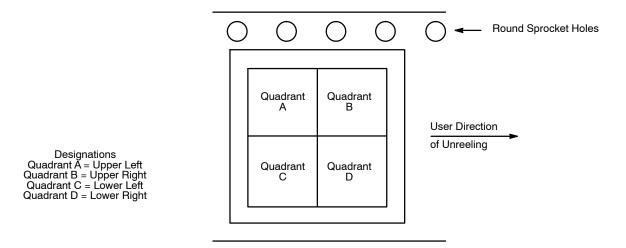


Figure 4. Tape and Reel Pin 1 Quadrant Orientation

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10EP51DG	SOIC-8 (Pb-Free)	98 Units / Rail
MC10EP51DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC10EP51DTG	TSSOP-8 (Pb-Free)	100 Units / Rail
MC10EP51MNTAG	DFN8 (Pb–Free)	1000 / Tape & Reel (Pin 1 Orientation in Quadrant A, Figure 4)
MC100EP51DG	SOIC-8 (Pb-Free)	98 Units / Rail
MC100EP51DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC100EP51DTG	TSSOP-8 (Pb-Free)	100 Units / Rail
MC100EP51DTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel

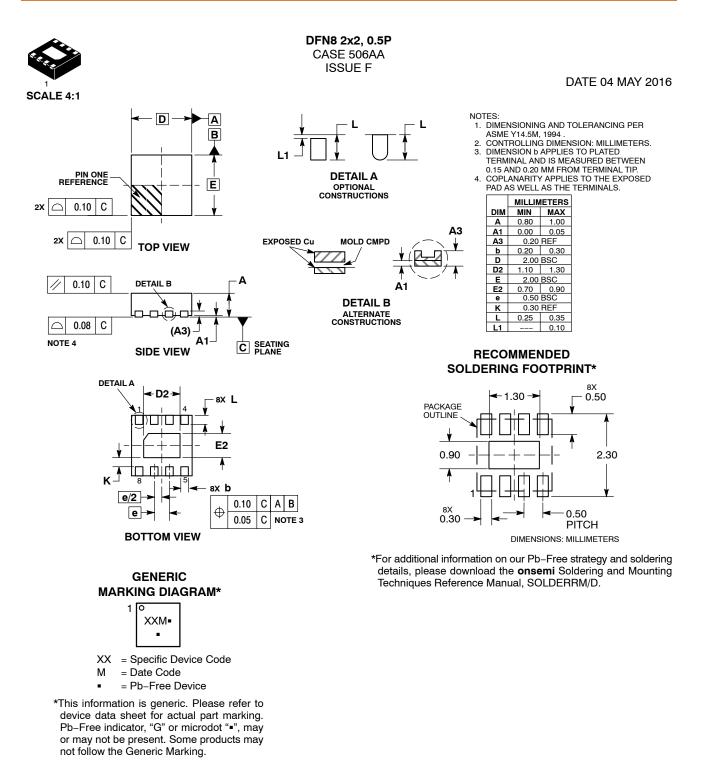
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

- AN1405/D-ECL Clock Distribution TechniquesAN1406/D-Designing with PECL (ECL at +5.0 V)AN1503/D-ECLinPS™ I/O SPiCE Modeling KitAN1504/D-Metastability and the ECLinPS FamilyAN1568/D-Interfacing Between LVDS and ECLAN1672/D-The ECL Translator GuideAND8001/D-Odd Number Counters Design
- AND8002/D Marking and Date Codes
- AND8020/D Termination of ECL Logic Devices
- AND8066/D Interfacing with ECLinPS
- AND8090/D AC Characteristics of ECL Devices

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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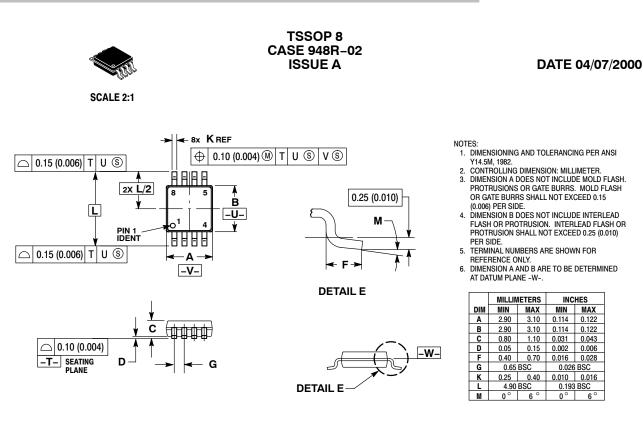
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